

Figure 1A  
Prior Art

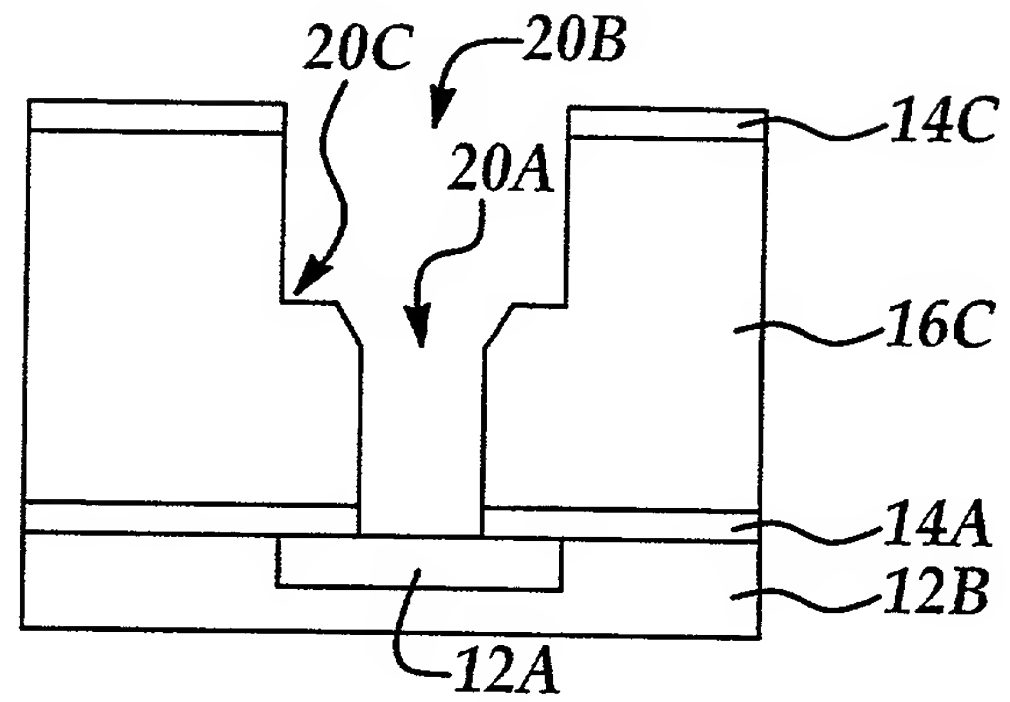


Figure 1B  
Prior Art

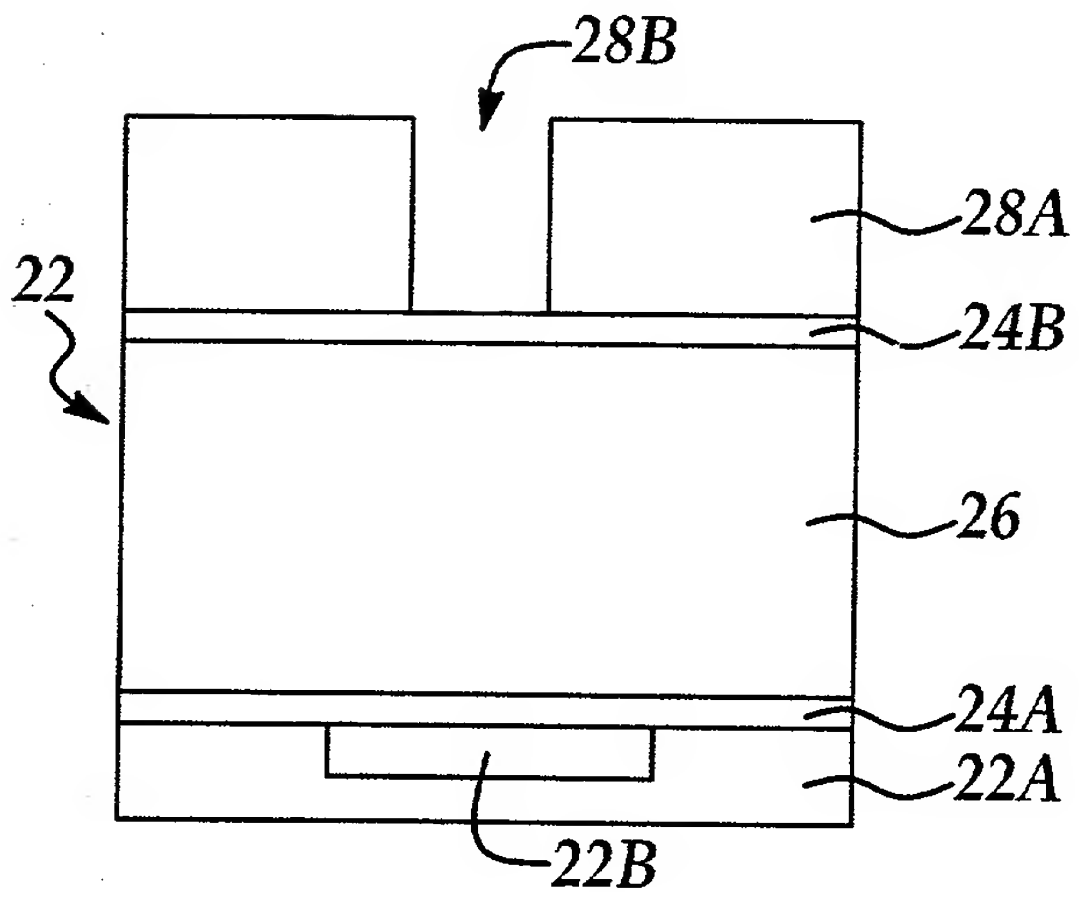


Figure 2A

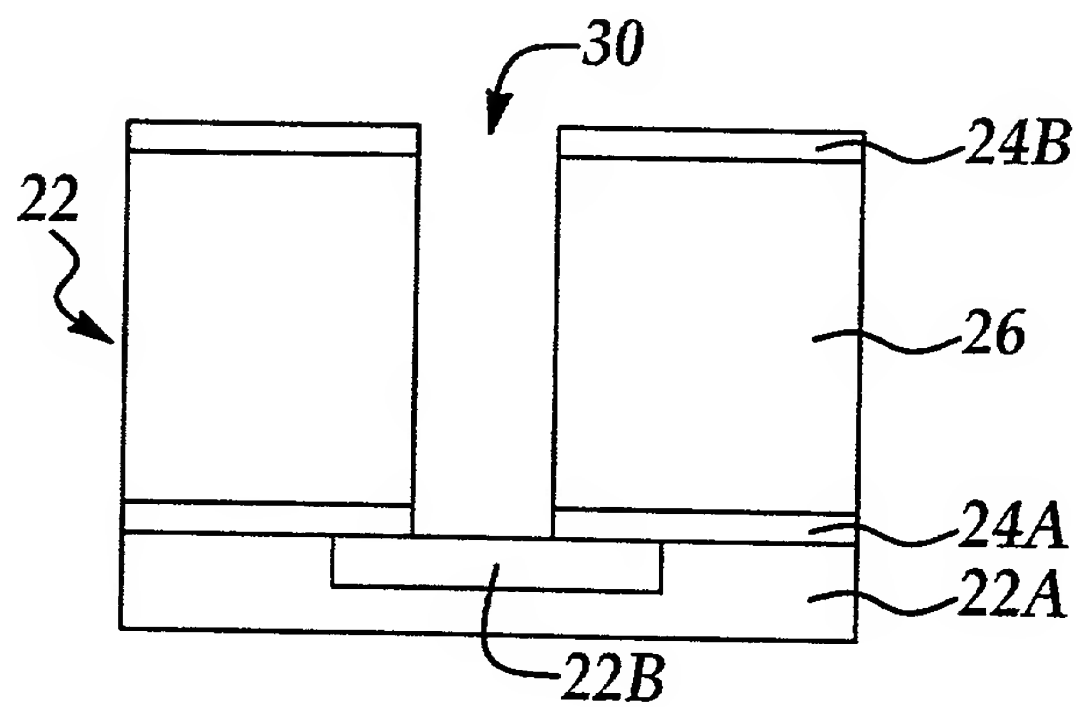


Figure 2B

A cross-sectional view of a semiconductor device. It features a central gap (30) between two main rectangular blocks (22 and 24). The left block (22) has a top layer (22A) and a bottom layer (22B). The right block (24) has a top layer (24A) and a bottom layer (24B). A central vertical structure (32) is located in the gap, with a wavy line (34) indicating a boundary or interface. A horizontal line (26) is shown within the right block. A horizontal line (32) is shown within the central gap structure.

This diagram shows a cross-sectional view of a semiconductor device. It features a central gap (36A) between two main structures. On the left, a structure (22) includes a top layer (28C), a middle layer (24B), and a bottom layer (24A). A central vertical feature (32) is located within this structure. On the right, a similar structure (26) is shown, also with layers 28C, 24B, and 24A. A central vertical feature (34) is located within this structure. A common base layer (22A) is at the bottom, with a central recessed area (22B). Arrows indicate the locations of the central gap (36A) and the left structure (22).

A cross-sectional view of a semiconductor device. The device features a central trench (30) with a bottom layer (32). The trench is flanked by two main regions (22, 26). The top surface of the device is covered by a thin layer (24B). The bottom of the device is a substrate (22A) with a central region (22B) that is recessed relative to the trench bottom. The side walls of the trench are labeled 24A.

Figure 2F

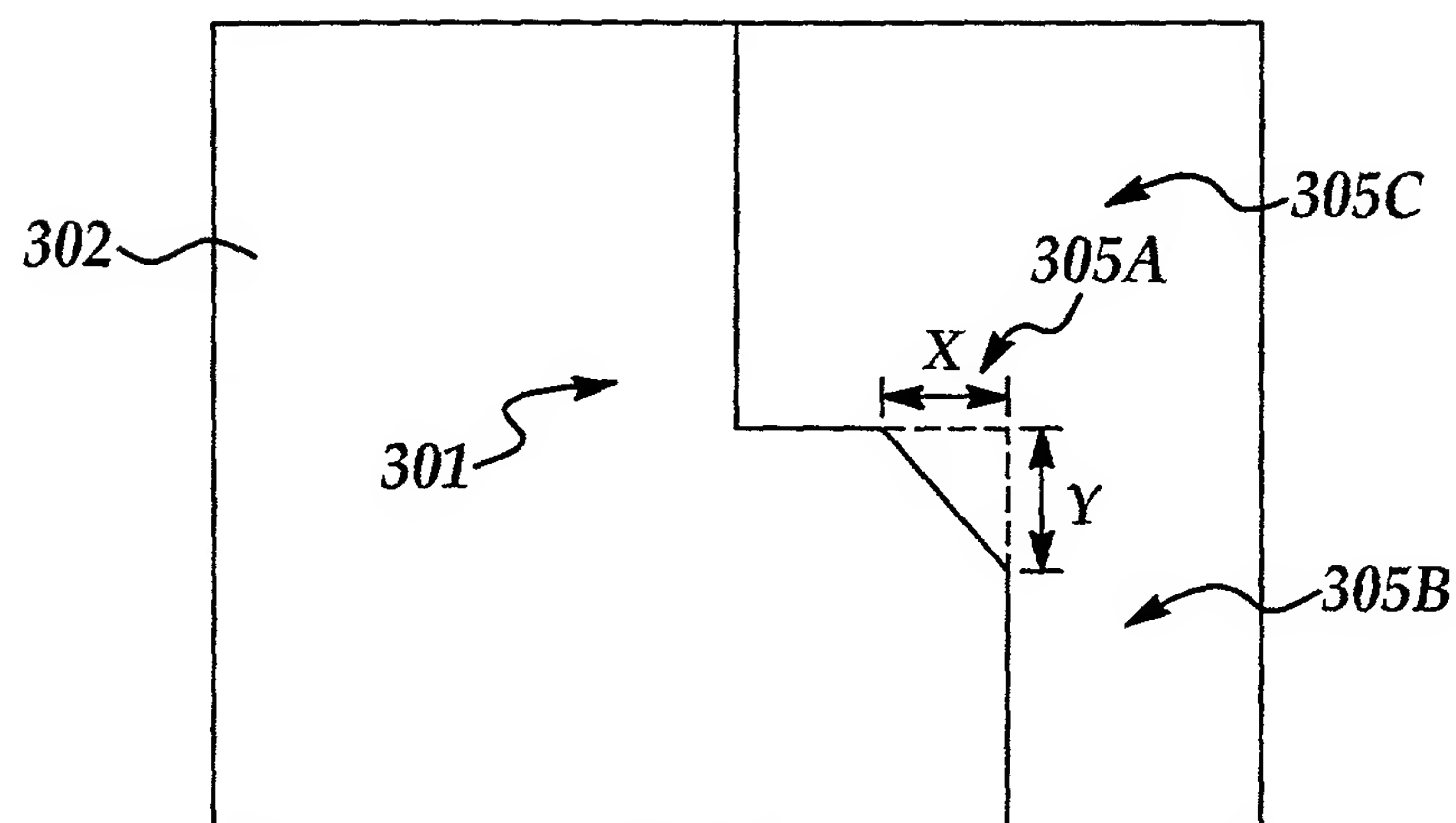


Figure 3A

SiON ETCH STOP LINER

THICKNESS (A)	0	100	200	300
FACET X DIMENSION	1000	800	570	710
FACET Y DIMENSION	1100	180	110	130

Figure 3B

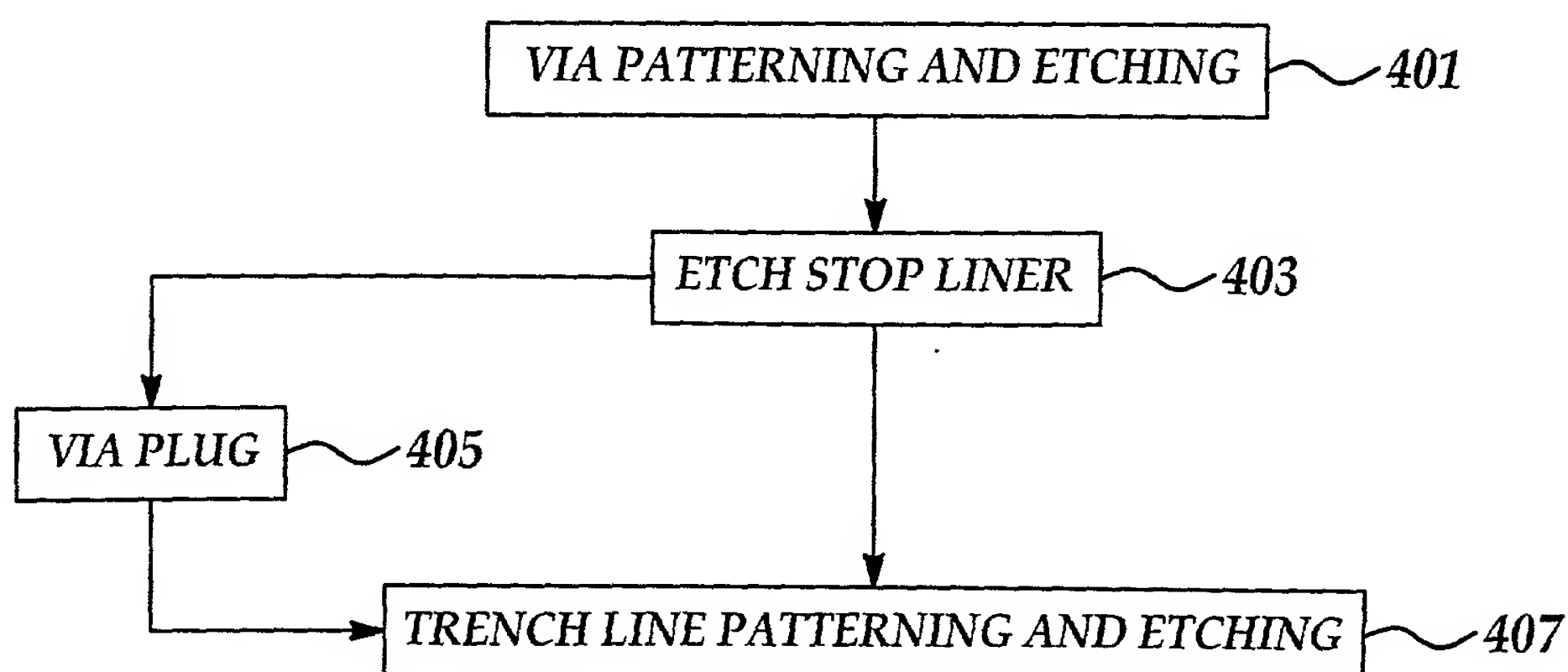


Figure 4